IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-6.   **(Cancelled)**

7.   **(Currently Amended)**   A silicon single crystal wafer which is a wafer prepared by means of a Czochralski method, the silicon single crystal <u>wafer</u> comprising at least one portion formed of an OSF ring portion in a peripheral region of the silicon single crystal <u>wafer</u> in contact with a boat on which the silicon single crystal <u>wafer</u> is placed for heat treatment.

8.   **(Previously Presented)**   A silicon single crystal wafer according to claim 7, wherein the OSF ring region is an annular region with a width of 10 mm or less from a periphery of the silicon single crystal wafer.

9.   **(Previously Presented)**   A silicon single crystal wafer according to claim 7, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1 x 10^{10} to 5 x 10^{15}/cm^3.

10.   **(Previously Presented)**   A silicon single crystal wafer according to claim 8, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1 x 10^{10} to 5 x 10^{15}/cm^3.

11.   **(Currently Amended)**   A manufacturing process for a silicon single crystal wafer comprising the steps of:

growing a silicon single crystal rod by means of a Czochralski method in a condition that an OSF ring region is formed in a peripheral region of the silicon single crystal rod; and

slicing the grown silicon ~~signal~~ <u>single</u> crystal rod into silicon single crystal wafers<u>,</u>

wherein the silicon single crystal wafer comprises at least one portion formed of the OSF ring portion in contact with a boat on which the silicon single crystal wafer is placed for heat treatment.

12.   (Previously Presented)   A manufacturing process for a silicon single crystal wafer according to claim 11, wherein a condition under which the OSF ring region is formed in a peripheral region of the silicon single crystal rod is such that when a pulling rate is indicated by F [mm/min] and an average temperature gradient in a pulling direction in a length between points corresponding to a silicon melting point and 1400°C in the crystal is indicated by G [°C/mm] by definition, there is present in a peripheral region of the crystal, an OSF ring region of a defect distribution chart which shows defect distribution, with an abscissa representing a distance [mm] in a direction to the crystal periphery from the center and an ordinate representing a value of F/G [mm^2/°C min].

13.   (Previously Presented)   A manufacturing process for a silicon single crystal wafer according to claim 11, wherein when a silicon single crystal rod is grown by means of the Czochralski method, the silicon single crystal rod is pulled while doping the silicon single crystal rod with nitrogen at a concentration in the range of 1 x 10^{10} to 5 x 10^{15}/cm^3.

14.   (Previously Presented)   A manufacturing process for a silicon single crystal wafer according to claim 12, wherein when a silicon single crystal rod is grown by means of the Czochralski method, the silicon single crystal rod is pulled while doping the silicon single crystal rod with nitrogen at a concentration in the range of 1 x 10^{10} to 5 x 10^{15}/cm^3.